Product data sheet

1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

1.2 Features and benefits

- Low thermal resistance
- Fast switching

1.3 Applications

- Electronic lighting ballast
- Inverters

- DC-to-DC converters
- Motor control systems

1.4 Quick reference data

- V_{CESM} ≤ 700 V
- Arr P_{tot} \leq 80 W

- $I_C \le 8 A$
- $h_{FEsat} = 11 (typ)$

2. Pinning information

Table 1. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	base		
2	collector	mb	2
3	emitter		
mb	mounting base; connected to collector	1 3	1 ————————————————————————————————————
		SOT428 (D-PAK)	

^[1] It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.



3. Ordering information

Table 2. Ordering information

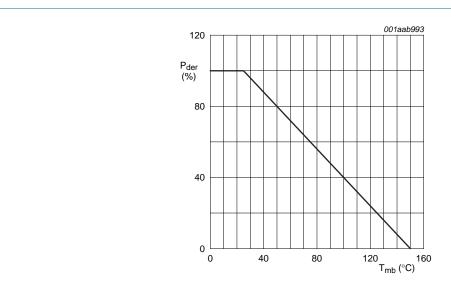
Type number	Package				
	Name	Description	Version		
BUJ105AD	D-PAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428		

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	peak collector-emitter voltage	$V_{BE} = 0 V$	-	700	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
V_{CBO}	collector-base voltage	open emitter	-	700	V
I _C	collector current (DC)		-	8	Α
I _{CM}	peak collector current		-	16	Α
I _B	base current (DC)		-	4	Α
I _{BM}	peak base current		-	8	Α
P _{tot}	total power dissipation	$T_{mb} = \le 25 ^{\circ}C$; see Figure 1	-	80	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25 \, ^{\circ}C)}} \times 100\%$$

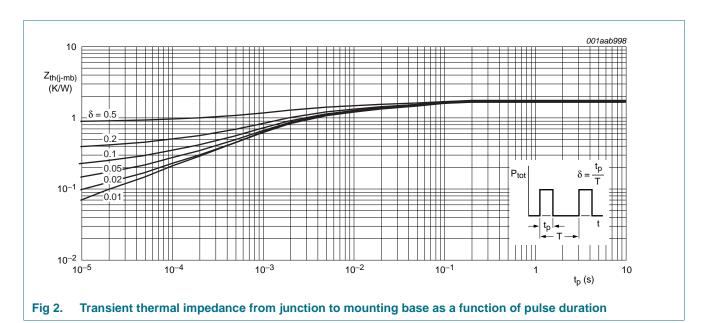
Fig 1. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> _	75	-	K/W

[1] Device mounted on a printed-circuit board; minimum footprint



6. Characteristics

 Table 5.
 Characteristics

 T_{mb} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
I _{CES}	collector-emitter cut-off current	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	<u>[1]</u>	-	-	0.2	mΑ
		$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}; T_j = 125 ^{\circ}\text{C}$	<u>[1]</u>	-	-	0.5	mA
I _{CBO}	collector-base cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}$	<u>[1]</u>	-	-	0.2	mΑ
I _{CEO}	collector-emitter cut-off current	V _{CEO} = V _{CEOMmax} = 400 V	<u>[1]</u>	-	-	0.1	mΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}$		-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage	$I_B = 0$ A; $I_C = 10$ mA; $L = 25$ mH; see Figure 3 and 4		400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 4.0 \text{ A}$; $I_B = 0.8 \text{ A}$; see <u>Figure 11</u>		-	0.3	1.0	V
V _{BEsat}	base-emitter saturation voltage	$I_C = 4.0 \text{ A}$; $I_B = 0.8 \text{ A}$; see Figure 12		-	1.0	1.5	V
h _{FE}	DC current gain	I _C = 1 mA; V _{CE} = 5 V		10	14	34	
		$I_C = 500 \text{ mA}$; $V_{CE} = 5 \text{ V}$; see Figure 10		13	23	36	
h _{FEsat}	DC saturation current gain	$I_C = 4.0 \text{ A}; V_{CE} = 5 \text{ V}$		8	11	15	



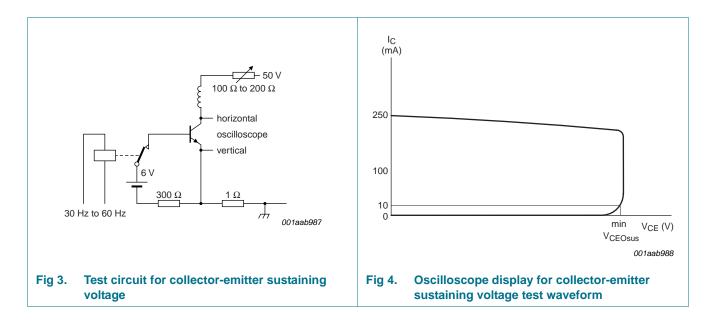
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 Table 5.
 Characteristics ...continued

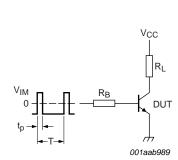
 $T_{mb} = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Switching	times (resistive load); see Figure 9	<u>5</u> and <u>6</u>				
t _{on}	turn-on time	$I_{Con} = 5 \text{ A}$; $I_{Bon} = -I_{Boff} = 1 \text{ A}$; $R_L = 75 \Omega$	-	0.65	1	μS
t _{stg}	storage time		-	1.8	2.5	μS
t _f	fall time		-	0.3	0.5	μS
Switching	times (inductive load); see Figure	<u>7</u> and <u>8</u>				
t _{stg}	storage time	$I_{Con} = 5 \text{ A}$; $I_{Bon} = 1 \text{ A}$; $L_{B} = 1 \mu \text{H}$;	-	1.2	1.7	μS
t _f	fall time	$V_{BB} = -5 \text{ V}$	-	20	50	ns
Switching times (inductive load); see Figure 7 and 8						
t _{stg}	storage time	$I_{Con} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; L_{B} = 1 \mu\text{H};$	-	1.4	1.9	μS
t _f	fall time	$V_{BB} = -5 \text{ V; } T_j = 100 ^{\circ}\text{C}$	-	25	100	ns

[1] Measured with half sine-wave voltage (curve tracer).



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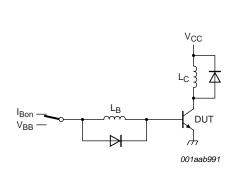
 V_{IM} = -6 V to +8 V; V_{CC} = 250 V; t_p = 20 $\mu s;$ $\delta = t_p/T = 0.01$.

 R_{B} and R_{L} calculated from I_{Con} and I_{Bon} requirements.

Ιc $\mathsf{I}_{\mathsf{Con}}$ 90 % ← ton I_{Bon} 10 % $t_r \le 30 \text{ ns}$ 001aab990

Switching times waveforms for resistive load Fig 6.





 V_{CC} = 300 V; V_{BB} = –5 V; L_{C} = 200 $\mu H;$ L_{B} = 1 $\mu H.$

Fig 7. Test circuit for inductive load switching

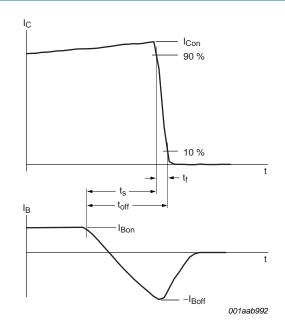
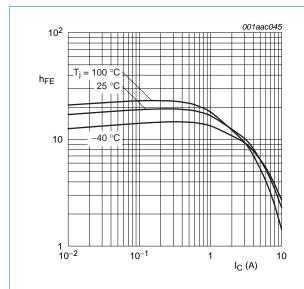


Fig 8. Switching times waveforms for inductive load

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DC current gain as a function of collector Fig 9. current; typical values at V_{CE} = 1 V

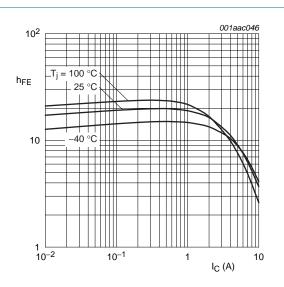


Fig 10. DC current gain as a function of collector current; typical values at V_{CE} = 5 V

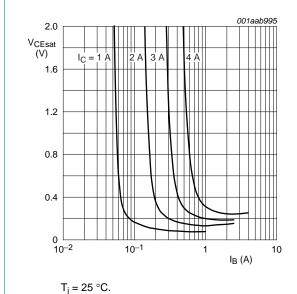


Fig 11. Collector-emitter saturation voltage as a function of base current; typical values

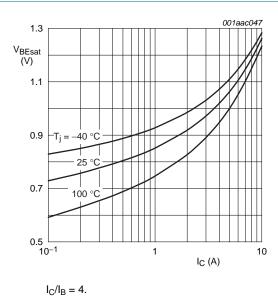


Fig 12. Base-emitter saturation voltage as a function of collector current; typical values

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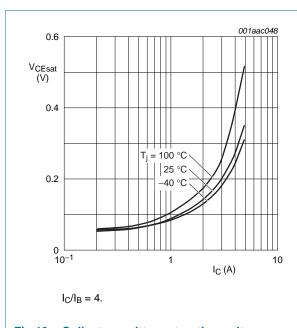


Fig 13. Collector-emitter saturation voltage as a function of collector current; typical values

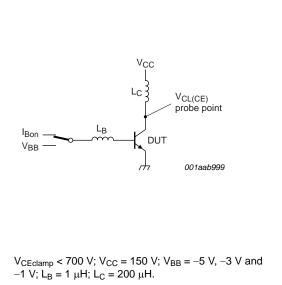
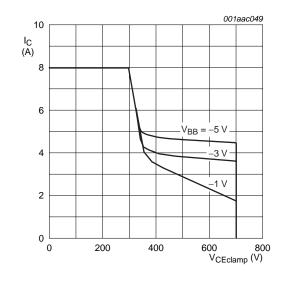


Fig 14. Test circuit for reverse bias safe operating



 $T_j < T_{j(max)}$.

Fig 15. Reverse bias safe operating area

7. Package information

Epoxy meets requirements of UL94 V-0 at ½ inch.

8. Package outline

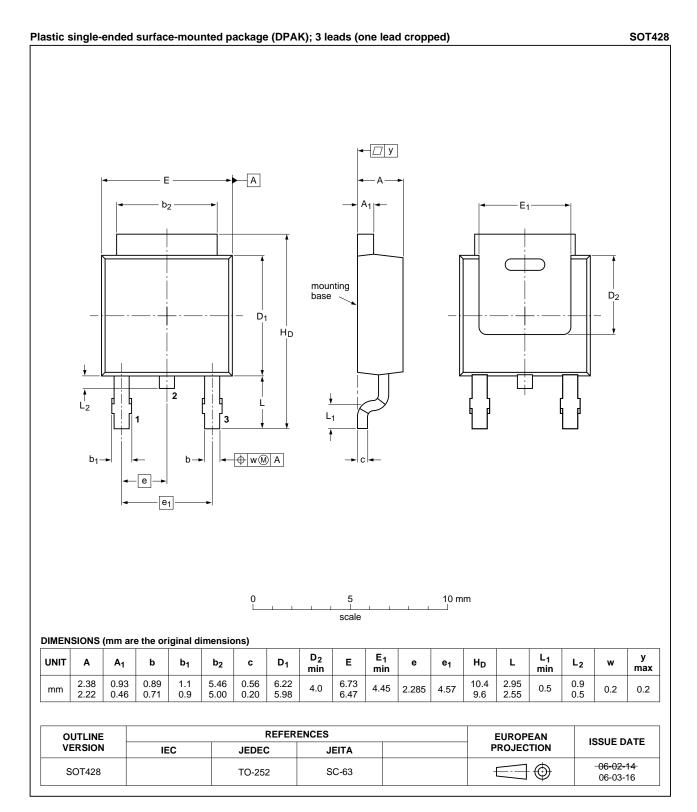
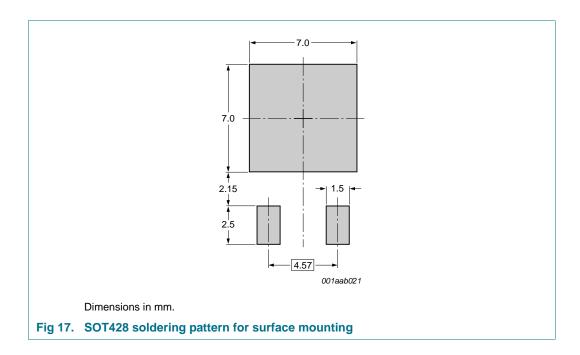


Fig 16. Package outline SOT428 (SC-63)

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9. Mounting



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10. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ105AD v.2	20111103	Product data sheet	-	BUJ105AD v.1
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts 	have been adapted to the	new company name whe	ere appropriate.
BUJ105AD v.1	20041214	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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